

SANYO	No.4232	2SJ256
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

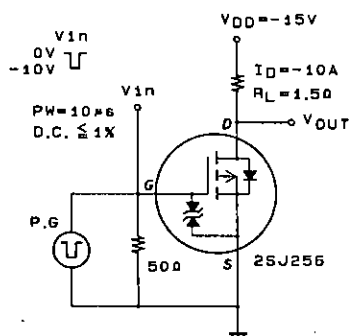
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

Absolute Maximum Ratings at Ta = 25°C

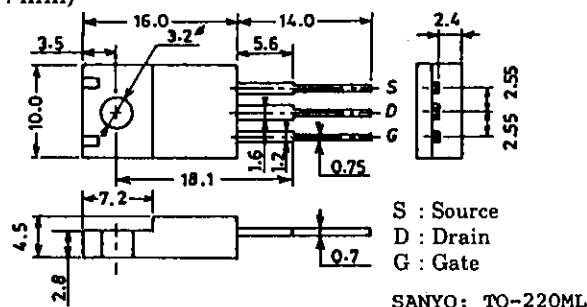
			unit
Drain to Source Voltage	V_{DS}	-30	V
Gate to Source Voltage	V_{GS}	± 15	V
Drain Current(DC)	I_D	-18	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-72 A
Allowable Power Dissipation	P_D	2.0	W
		$T_c = 25^\circ C$	30 W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-30			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -10A$	8.5	14		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -10A, V_{GS} = -10V$		40	55	m Ω
	$R_{DS(on)}$	$I_D = -10A, V_{GS} = -4V$		55	75	m Ω
Input Capacitance	C_{iss}	$V_{DS} = -10V, f = 1MHz$		2000		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V, f = 1MHz$		1200		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10V, f = 1MHz$		440		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		18		ns
Rise Time	t_r	"		50		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		400		ns
Fall Time	t_f	"		400		ns
Diode Forward Voltage	V_{SD}	$I_S = -18A, V_{GS} = 0$	-1.0	-1.5		V

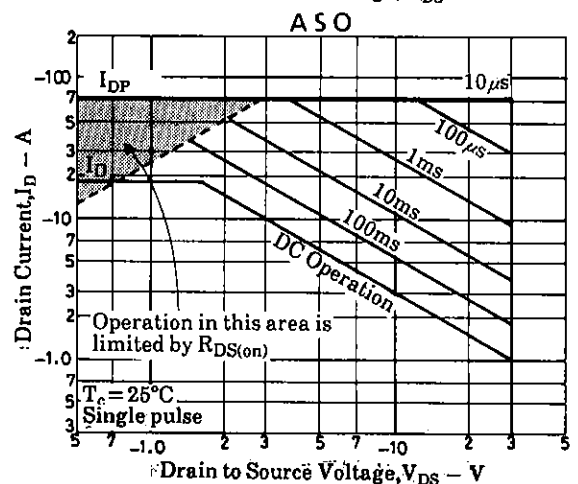
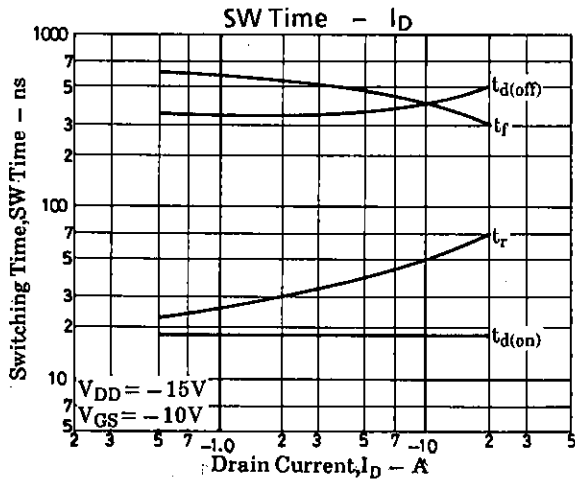
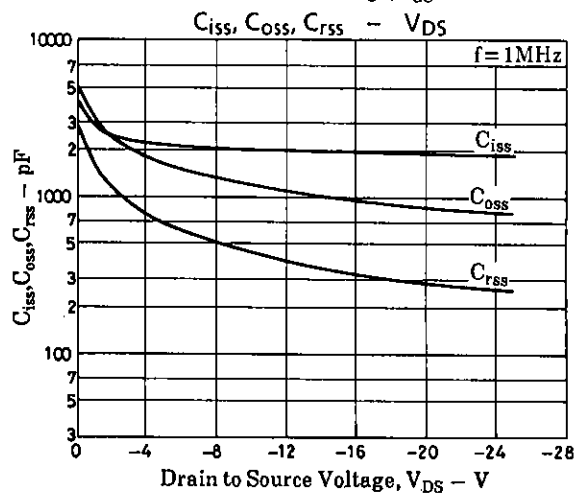
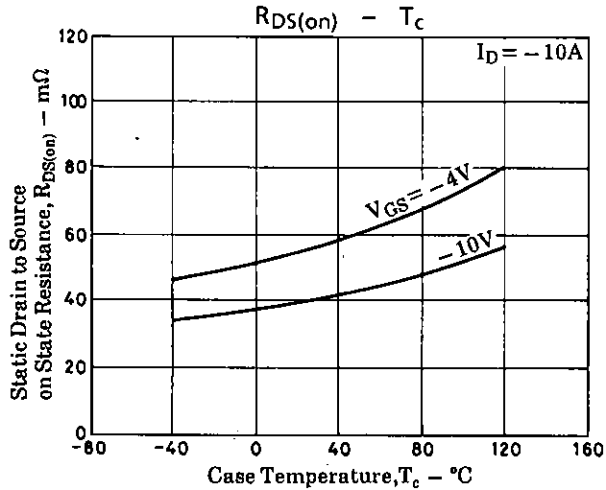
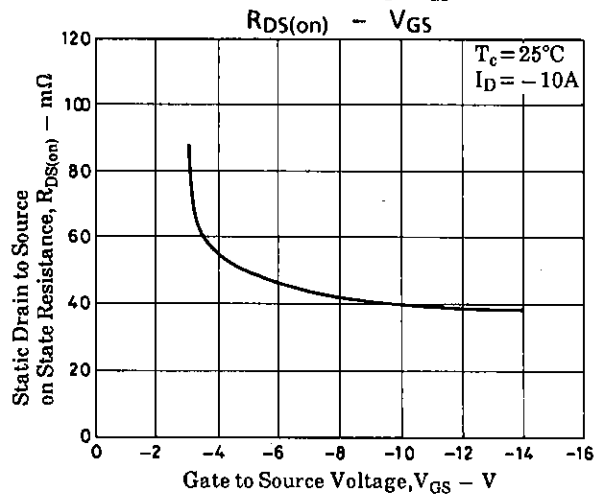
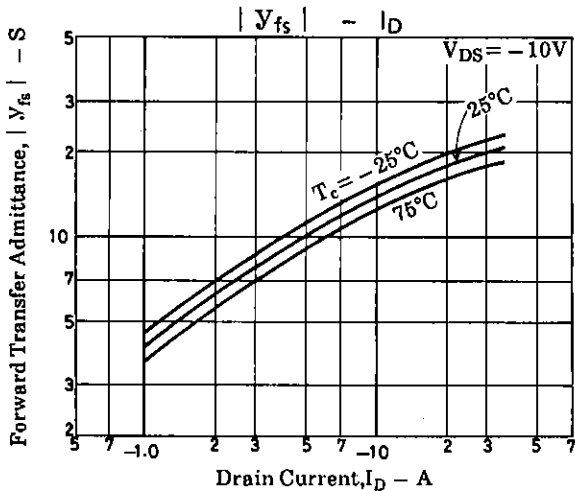
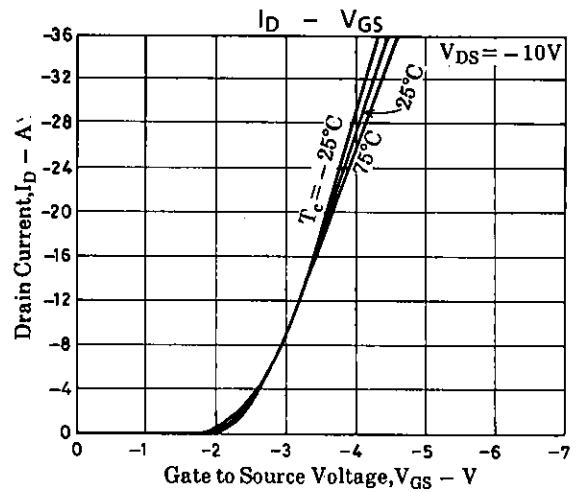
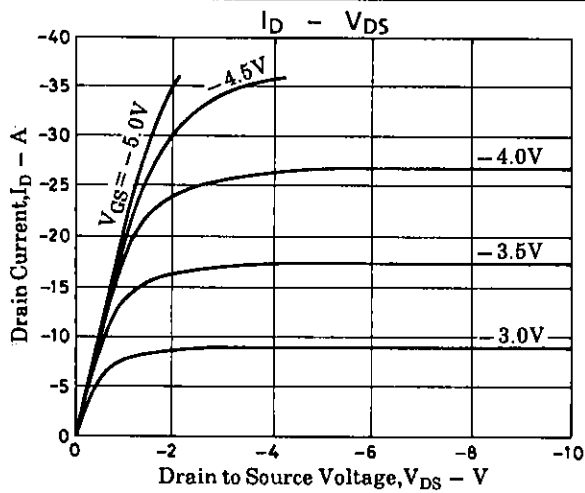
Switching Time Test Circuit**Package Dimensions 2063**

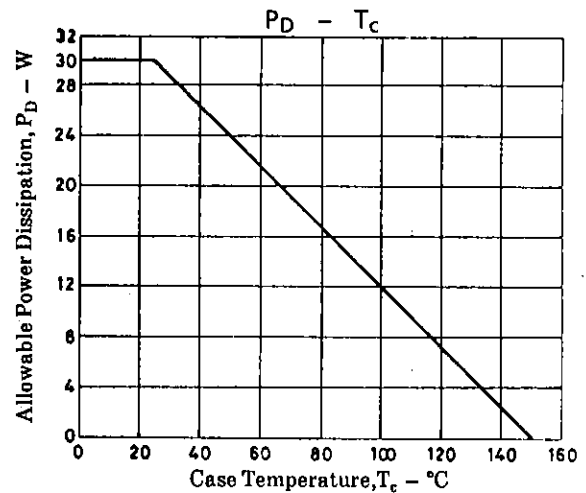
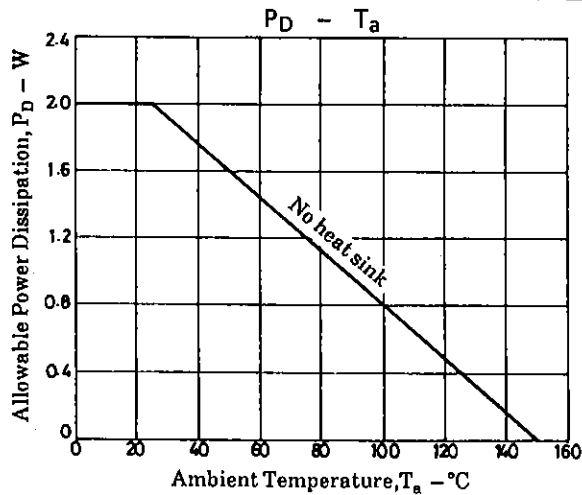
(unit : mm)



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